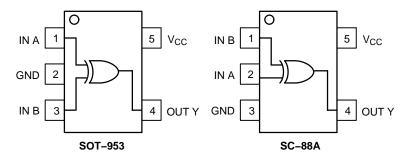
Single 2-Input XOR Gate

The NL17SG86 MiniGate[™] is an advanced high–speed CMOS 2–State XOR gate in ultra–small footprint.

The NL17SG86 input structures provides protection when voltages up to 4.6 V are applied.

Features

- Wide Operating V_{CC} Range: 0.9 V to 3.6 V
- High Speed: $t_{PD} = 2.7$ ns (Typ) at $V_{CC} = 3.0$ V, $C_L = 15$ pF
- Low Power Dissipation: $I_{CC} = 0.5 \ \mu A \ (Max)$ at $T_A = 25^{\circ}C$
- 4.6 V Overvoltage Tolerant (OVT) Input Pins ($V_{CC} \ge 0.9 \text{ V}$)
- Ultra-Small Packages
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant



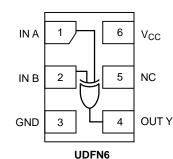


Figure 1. Pinouts (Top View)

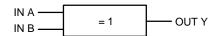
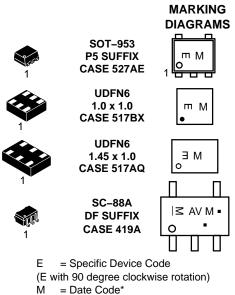


Figure 2. Logic Symbol



ON Semiconductor®

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- = Date Code"
- = Pb-Free Package
- (Note: Microdot may be in either location)

*Date Code orientation and/or position may vary depending upon manufacturing location.

	PIN ASSIGNMENT					
	SOT-953	SC-88A	UDFN6			
1	IN A	IN B	IN A			
2	GND	IN A	IN B			
3	IN B	GND	GND			
4	OUT Y	OUT Y	OUT Y			
5	V _{CC}	V _{CC}	NC			
6			V _{CC}			

FUNCTION TABLE

A Input	OE Input	Y Output
L	L	L
L	н	н
н	L	н
Н	Н	L

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

MAXIMUM RATINGS

Symbol	Parame	eter	Value	Unit
V _{CC}	DC Supply Voltage		–0.5 to +5.5	V
V _{IN}	DC Input Voltage		–0.5 to +4.6	V
V _{OUT}	DC Output Voltage	Output at High or Low State Power–Down Mode ($V_{CC} = 0 V$)	-0.5 to V _{CC} +0.5 -0.5 to +4.6	V
I _{IK}	DC Input Diode Current	V _{IN} < GND	-20	mA
Ι _{ΟΚ}	DC Output Diode Current	V _{OUT} < GND	-20	mA
I _{OUT}	DC Output Source/Sink Current		±20	mA
I _{CC}	DC Supply Current per Supply Pin		±20	mA
I _{GND}	DC Ground Current per Ground Pin		±20	mA
T _{STG}	Storage Temperature Range		-65 to +150	°C
ΤL	Lead Temperature, 1 mm from Case for 10 S	econds	260	°C
TJ	Junction Temperature Under Bias		+150	°C
MSL	Moisture Sensitivity		Level 1	
F _R	Flammability Rating	Oxygen Index: 28 to 34	UL 94 V–0 @ 0.125 in	
V_{ESD}	ESD Withstand Voltage	Human Body Model (Note 2) Machine Model (Note 3)	>2000 >100	V
ILATCHUP	Latchup Performance Abov	ve V _{CC} and Below GND at 125°C (Note 4)	±100	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.
Measured with minimum pad spacing on an FR4 board, using 10 mm-by-1 inch, 2-ounce copper trace with no air flow.
Tested to EIA/JESD22-A114-A.
Tested to EIA/JESD22-A115-A.

4. Tested to EIA/JESD78.

RECOMMENDED OPERATING CONDITIONS

Symbol	Characteristics	Min	Max	Unit
V _{CC}	Positive DC Supply Voltage	0.9	3.6	V
V _{IN}	Digital Input Voltage	0.0	3.6	V
V _{OUT}	Output Voltage Output at High or Low State Power-Down Mode (V _{CC} = 0 V)		V _{CC} 3.6	V
T _A	Operating Temperature Range	-55	+125	°C
Δt / ΔV	Input Transition Rise or Fail Rate V_{CC} = 3.3 V ± 0.3 V	0	10	ns/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

DC ELECTRICAL CHARACTERISTICS

					T _A =	25°C	$T_A = -55^{\circ}C$	C to +125°C	
Symbol	Parameter	C	onditions	V _{CC} (V)	Min	Max	Min	Max	Unit
VIH	High-Level			0.9	V _{CC}		V _{CC}		V
	Input Voltage			1.1 to 1.3	0.7xV _{CC}		0.7xV _{CC}		
				1.4 to 1.6	0.65xV _{CC}		$0.65 \mathrm{xV}_{\mathrm{CC}}$		
				1.65 to 1.95	0.65xV _{CC}		$0.65 \mathrm{xV}_{\mathrm{CC}}$		
				2.3 to 2.7	1.7		1.7		
				3.0 to 3.6	2.0		2.0		
VIL	Low-Level Input			0.9		GND		GND	V
	Voltage			1.1 to 1.3		0.3xV _{CC}		0.3xV _{CC}	
				1.4 to 1.6		0.35xV _{CC}		0.35xV _{CC}	
				1.65 to 1.95		0.35xV _{CC}		0.35xV _{CC}	
				2.3 to 2.7		0.7		0.7	
				3.0 to 3.6		0.8		0.8	
V _{OH}	Output Voltage VIII Or	V _{IN} =	I _{OH} = -20 μA	0.9	0.75		0.75		V
		I _{OH} = -0.3 mA	1.1 to 1.3	0.75xV _{CC}		0.75xV _{CC}			
			I _{OH} = -1.7 mA	1.4 to 1.6	0.75xV _{CC}		0.75xV _{CC}		
			I _{OH} = -3.0 mA	1.65 to 1.95	V _{CC} -0.45		V _{CC} -0.4 5		
			$I_{OH} = -4.0 \text{ mA}$	2.3 to 2.7	2.0		2.0		
			I _{OH} = -8.0 mA	3.0 to 3.6	2.48		2.48		
V _{OL}	Low-Level	V _{IN} =	I _{OL} = 20 μA	0.9		0.1		0.1	V
	Output Voltage	V _{IH} or V _{IL}	l _{OL} = 0.3 mA	1.1 to 1.3		$0.25 \mathrm{xV}_{\mathrm{CC}}$		0.25xV _{CC}	
			l _{OL} = 1.7 mA	1.4 to 1.6		$0.25 \mathrm{xV}_{\mathrm{CC}}$		0.25xV _{CC}	
			I _{OL} = 3.0 mA	1.65 to 1.95		0.45		0.45	
			I _{OL} = 4.0 mA	2.3 to 2.7		0.4		0.4	
			I _{OL} = 8.0 mA	3.0 to 3.6		0.4		0.4	
I _{IN}	Input Leakage Current	0 ≤	$V_{IN} \le 3.6 V$	0 to 3.6		±0.1		±1.0	μΑ
I _{CC}	Quiescent Supply Current	V _{IN} =	V _{CC} or GND	3.6		0.5		10.0	μΑ

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

Symbol	Parameter	Test Condition	V _{CC} (V)	T _A = 25°C		$T_A = -55^{\circ}C$	C to +125°C	Unit	
				Min	Тур	Max	Min	Мах	
t _{PLH} ,	Propagation Delay,	C _L = 10 pF,	0.9	-	23	-	-	-	ns
t _{PHL}	A or B to Y	$R_{L} = 1 M\Omega$	1.1 to 1.3	-	11.7	20.9	-	39.1	
			1.4 to 1.6	-	6.7	10.0	-	11.8	
			1.65 to 1.95	-	5.1	6.6	-	7.6	
			2.3 to 2.7	-	3.4	4.1	-	4.7	
			3.0 to 3.6	-	2.7	3.3	-	3.9	
		C _L = 15 pF,	0.9	-	23.7	-	-	-	ns
	RL	$R_{L} = 1 M\Omega$	1.1 to 1.3	-	11.9	22.8	-	39.4	•
			1.4 to 1.6	-	6.7	9.9	-	11.9	
			1.65 to 1.95	-	5.1	7.3	-	7.5	
			2.3 to 2.7	-	3.4	4.7	-	5.3	
			3.0 to 3.6	-	2.7	3.6	-	4.1	
		$C_{L} = 30 \text{ pF},$	0.9	-	32.1	-	-	-	ns
		$R_{L} = 1 M\Omega$	1.1 to 1.3	-	15.7	31.4	-	59.4	
		1.4 to 1.6	-	8.7	13.9	-	16.9		
			1.65 to 1.95	-	6.5	9.8	-	10.2	
			2.3 to 2.7	-	4.2	6.0	-	6.5	
			3.0 to 3.6	-	3.4	4.7	-	5.1	
C _{IN}	Input Capacitance		0 to 3.6		3	-	-	-	pF
CO	Output Capacitance	V _O = GND	0		3	-	-	-	pF
C _{PD}	Power Dissipation Capacitance (Note 5)	f = 10 MHz	0.9 to 3.6	-	4	-	_	-	pF

AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3.0$ ns)

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.
C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the dynamic operating current consumption without load. Average operating current can be obtained by the equation: I_{CC(OPR)} = C_{PD} • V_{CC} • f_{in} + I_{CC}. C_{PD} is used to determine the no–load dynamic power consumption; P_D = C_{PD} • V_{CC}² • f_{in} + I_{CC} • V_{CC}.

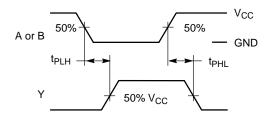
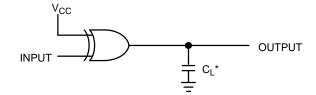


Figure 3. Switching Waveform



*Includes all probe and jig capacitance. A 1 MHz square input wave is recommended for propagation delay tests.

Figure 4. Test Circuit

ORDERING INFORMATION

Device	Package	Shipping [†]
NL17SG86P5T5G	SOT–953 (Pb–Free)	8000 / Tape & Reel
NL17SG86DFT2G	SC-88A (Pb-Free)	3000 / Tape & Reel
NL17SG86AMUTCG*	UDFN6 1.45 x 1 mm (Pb-Free)	3000 / Tape & Reel
NL17SG86CMUTCG*	UDFN6 1 x 1 mm (Pb–Free)	3000 / Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

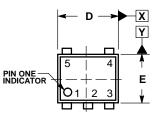
*In Development.

PACKAGE DIMENSIONS

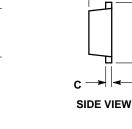
SOT-953 CASE 527AE ISSUE E

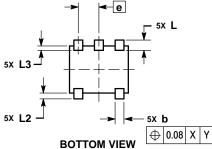
 H_{E}

Α



TOP VIEW

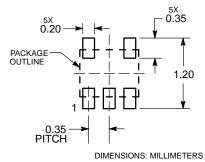




- NOTES:
 DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 CONTROLLING DIMENSION: MILLIMETERS
 MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
 DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

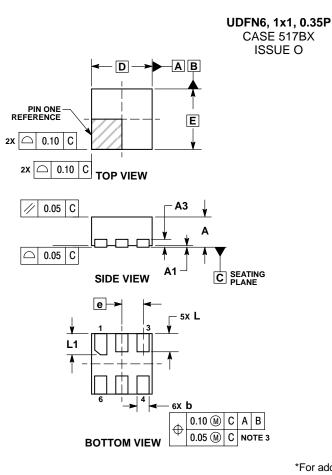
FLAS	H, PRO	RUSIO	NS, OR (
	MIL	MILLIMETERS					
DIM	MIN NOM MAX						
Α	0.34	0.37	0.40				
b	0.10	0.15	0.20				
С	0.07	0.12	0.17				
D	0.95	1.00	1.05				
Е	0.75	0.80	0.85				
е		0.35 BS	С				
ΗE	0.95	1.00	1.05				
L	0.175 REF						
L2	0.05	0.10	0.15				
L3			0.15				

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

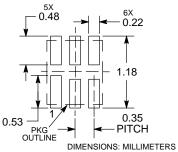
PACKAGE DIMENSIONS



- NOTES: 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994. 2. CONTROLLING DIMENSION: MILLIMETERS. 3. DIMENSION & APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.20 MM FROM TERMINAL TIP. 4. PACKAGE DIMENSIONS EXCLUSIVE OF BURRS AND MOLD FLASH.

	MILLIN	MILLIMETERS				
DIM	MIN	MAX				
Α	0.45	0.55				
A1	0.00	0.05				
A3	0.13 REF					
b	0.12	0.22				
D	1.00	BSC				
E	1.00	BSC				
е	0.35	BSC				
L	0.25	0.35				
L1	0.30	0.40				

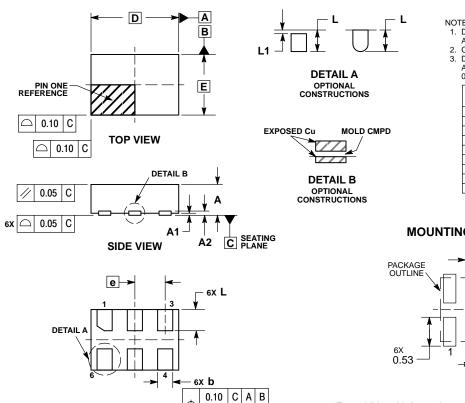
RECOMMENDED SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

UDFN6, 1.45x1.0, 0.5P CASE 517AQ ISSUE O



Φ

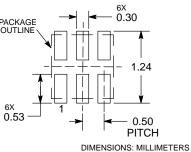
BOTTOM VIEW

0.05 C NOTE 3

NOTES:
 DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 CONTROLLING DIMENSION: MILLIMETERS.
 DIMENSION & APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.30 mm FROM THE TERMINAL TIP.

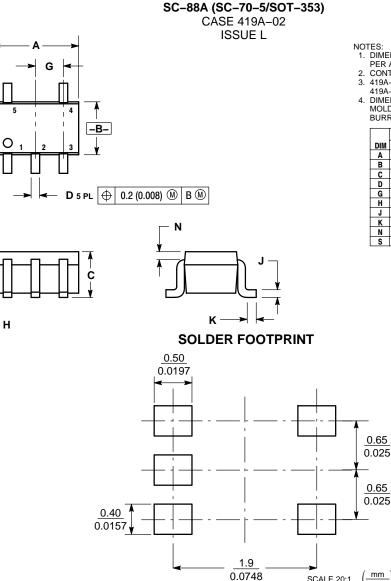
	MILLIM	ETERS
DIM	MIN	MAX
Α	0.45	0.55
A1	0.00	0.05
A2	0.07	REF
b	0.20	0.30
D	1.45	BSC
Е	1.00	BSC
е	0.50	BSC
L	0.30	0.40
L1		0.15

MOUNTING FOOTPRINT



*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS



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DIES.
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 CONTROLLING DIMENSION: INCH.
 419A-01 OBSOLETE. NEW STANDARD

419A-02

DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	INC	HES	MILLIMETER		
DIM	MIN	MAX	MIN	MAX	
Α	0.071	0.087	1.80	2.20	
В	0.045	0.053	1.15	1.35	
С	0.031	0.043	0.80	1.10	
D	0.004	0.012	0.10	0.30	
G	0.026	BSC	0.65 BSC		
Н		0.004		0.10	
ſ	0.004	0.010	0.10	0.25	
Κ	0.004	0.012	0.10	0.30	
Ν	0.008 REF		0.20	REF	
s	0.079	0.087	2.00	2.20	